



Parameter	Symbol	Rating	Unit		
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	±20	V	
		I _D (T _c =25 °C)	300 A		
		P _D (T _c =100 °C)	30 W		
		D _M (T _c =25 °C)	1200 A		
Power Dissipation		P _D (T _c =25 °C)	375 W		
Operating and Storage Temperature Range		T _J , T _{stg}	-55 to 175	Min	Typ
		(T _c =25 °C)	300 A		
		E _{AS}	1512	mJ	
		θ _{JA}	60		

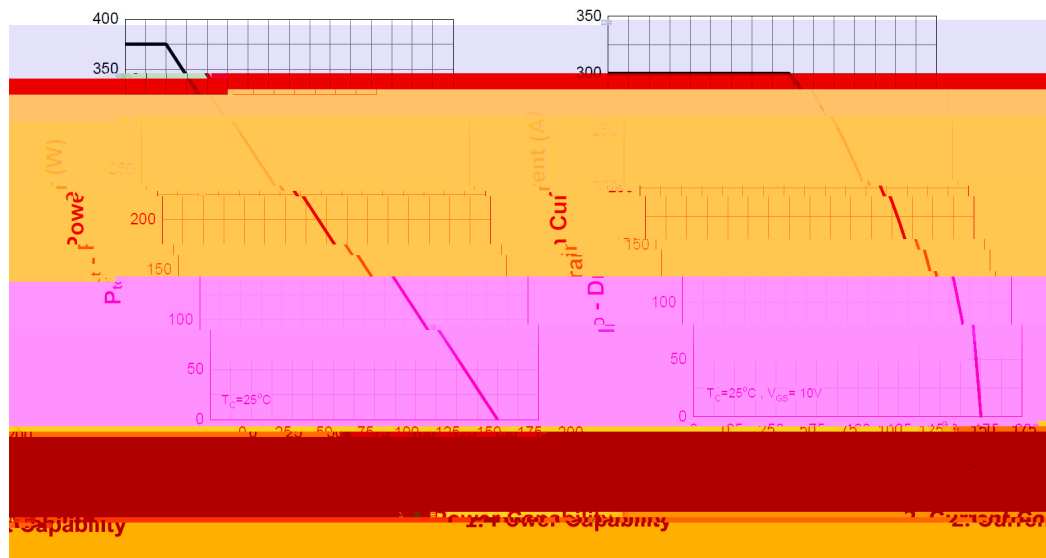
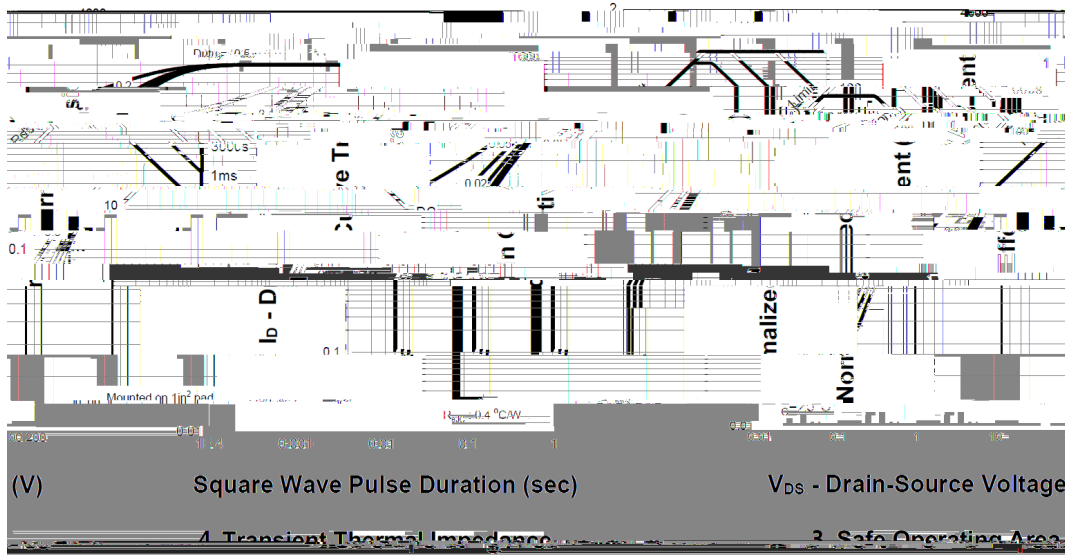
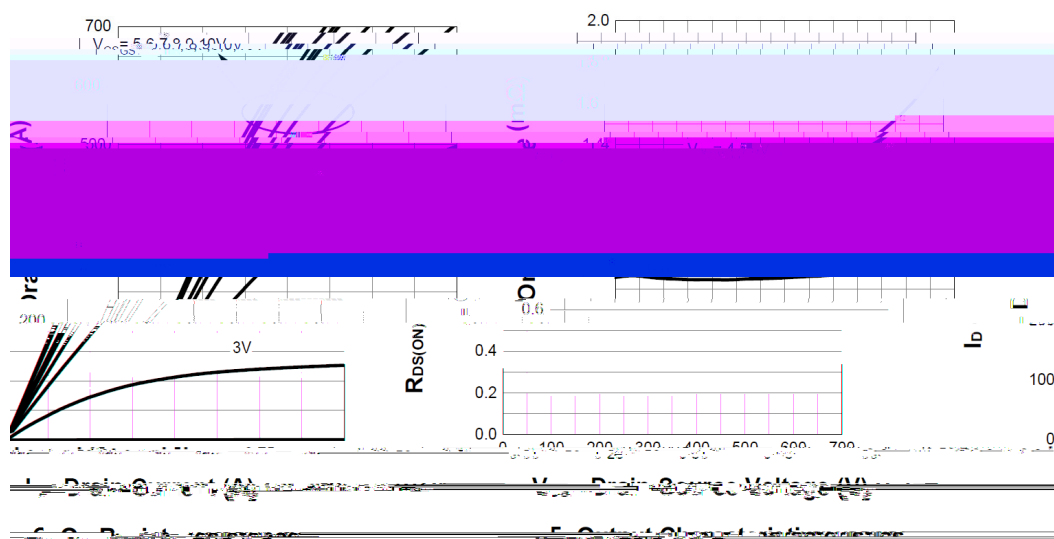
DD=40V, L=1.0mH)

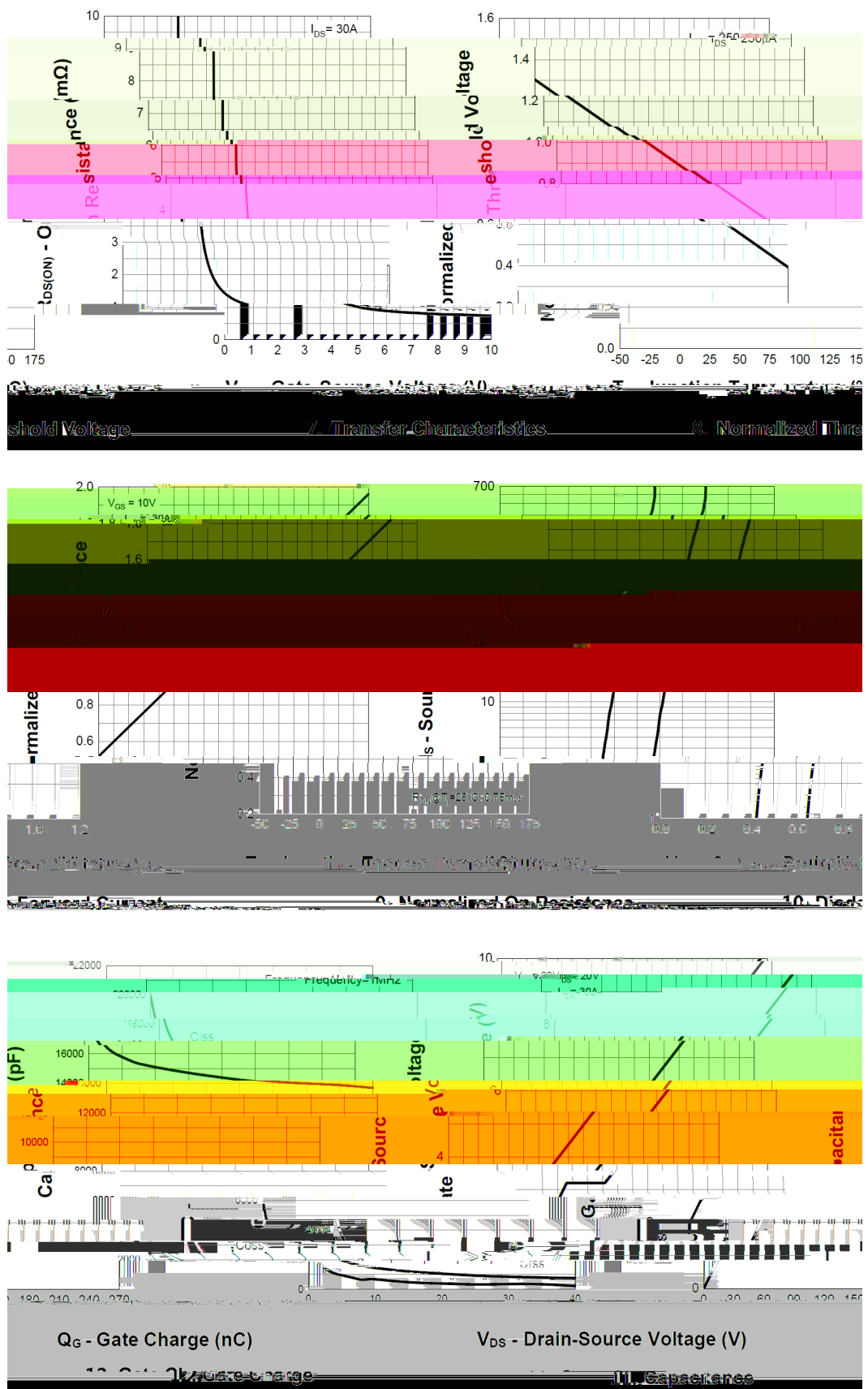
Thermal resistance, junction – case

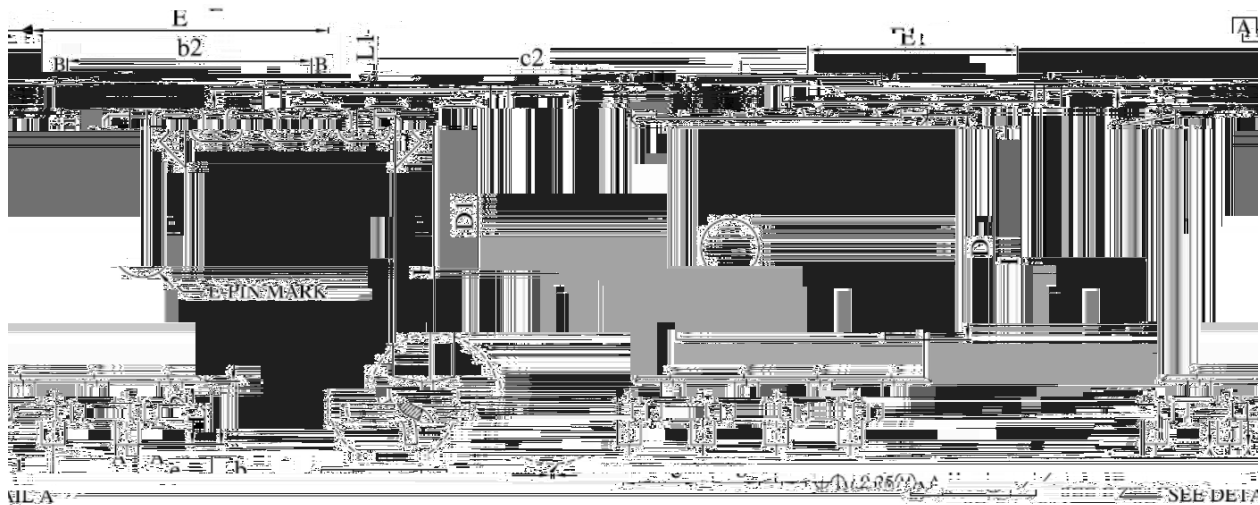
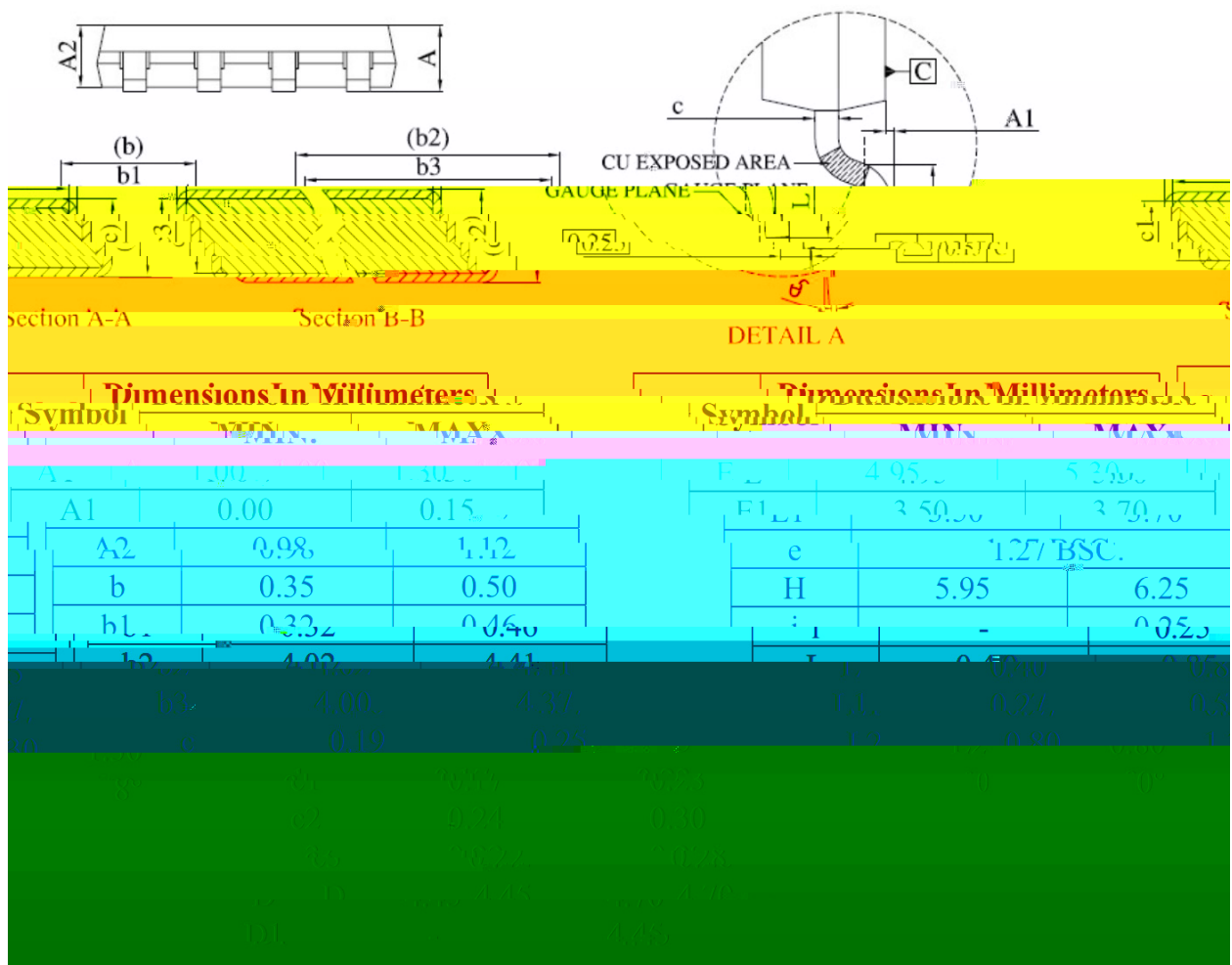
2 pad area, t ≤ 10 sec 2. Pulse width ≤ 300 μs, duty cycle ≤ 2 % 3. limited by bonding wire

Drain-Source Breakdown Voltage	BV	V _{GS} =0V	I _D =250μA	40		V
	GS(th)	V	DS=V _{GS}	I _D =250μA	1.0	2.0
		V _{GS} =0V	V _{DS} =0V			1 μA
	GSS	V _{GS} =±20V	V _{DS} =0V			±0.1 μA
On-Resistance	r _{DS(on)}	V _{GS} =4.5V	I _D =20A	0.75	0.85	mΩ
Drain-Source Diode Forward	SD	V _{GS} =0V	I _S =30A		1.15	1.45 mΩ
		I _S =30 A, V _{GS} = 0 V dI _S /dt = 100 A/μs		21	nS	1.3 V
Input Capacitance	C _{iss}	V _{DS} =20V	V _{GS} =0V		14406	pF
Output Capacitance	C _{oss}	f=1.0MHz			1043	
Reverse Transfer Capacitance	Crss				369	

Parameter









BR

008N04S

Note

BR: Company Code

008N04S: Product Type Code

****: Lot No. Code, code change with Lot No.

